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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-40
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.029
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.047
I <sub>D</sub> (A)	-16
Configuration	Single
Package	PowerPAK 1212-8W

### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

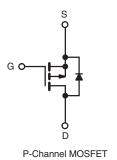




ROHS COMPLIANT HALOGEN FREE







PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	-40		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current a	T <sub>C</sub> = 25 °C	1	-16		
Continuous Drain Current "	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-16		
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	-16	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-64		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	-26		
Single Pulse Avalanche Energy	L=0.1 min	E <sub>AS</sub>	33.8	mJ	
Mariana Damas Disaination h	T <sub>C</sub> = 25 °C	D	62.5	14/	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	5°C P <sub>D</sub> 20		W	
Operating Junction and Storage Temperature Ran	nge	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Temperature)		260	-0		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	$R_{thJA}$	81	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.4	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	_			•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μA	-40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \ge 5 V$	-20	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A	-	0.020	0.029	
Dunin Course On Chata Basistana 3	Б	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A, T <sub>J</sub> = 125 °C	-	0.030	0.043	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A, T <sub>J</sub> = 175 °C	-	0.040	0.051	Ω
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -9 A	-	0.035	0.047	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> :	= -15 V, I <sub>D</sub> = -7 A	-	12	-	S
Dynamic <sup>b</sup>							•
Input Capacitance	C <sub>iss</sub>			-	1565	1875	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = -20 \text{ V, f} = 1 \text{ MHz}$	-	245	295	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	170	205	
Total Gate Charge c	$Q_g$			-	17.7	21.2	
Gate-Source Charge c	Q <sub>gs</sub>	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -20 \text{ V}, I_{D} = -9.3 \text{ A}$	-	5.6	6.6	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	8.1	9.7	
Gate Resistance	$R_{g}$	f = 1 MHz		1.1	1.95	2.8	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	14	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} =$	-20 V, $R_L$ = 14.2 Ω	-	10	13	
Turn-Off Delay Time c	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -1.4 A,	$V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	36.5	44	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	10.2	13	1
Source-Drain Diode Ratings and Chara	acteristic <sup>b</sup>	•			•		
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-64	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = -8.8 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.1	V

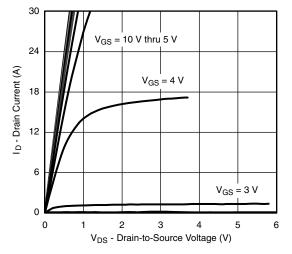
#### **Notes**

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

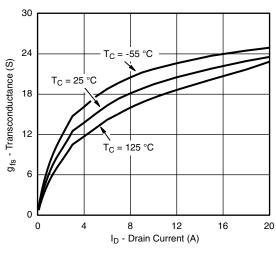
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



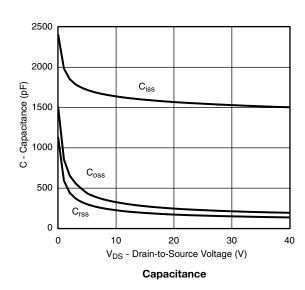
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

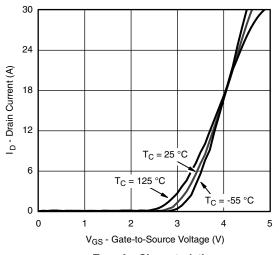


#### **Output Characteristics**

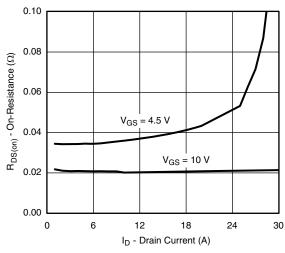


### Transconductance

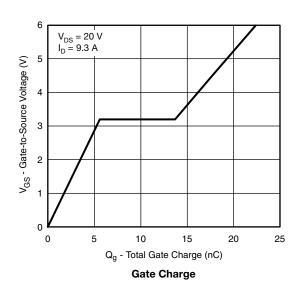




#### **Transfer Characteristics**

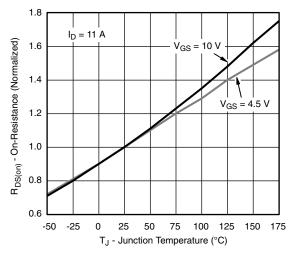


### **On-Resistance vs. Drain Current**

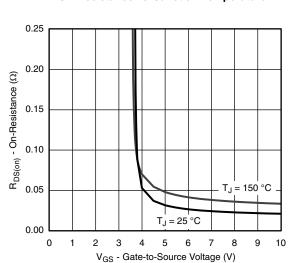




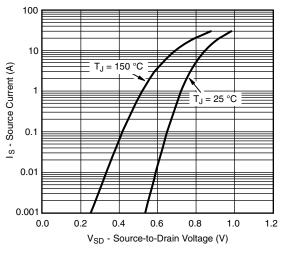
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



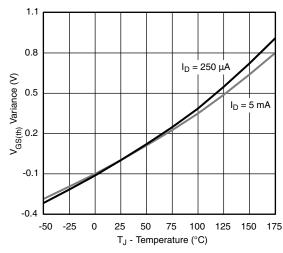
On-Resistance vs. Junction Temperature



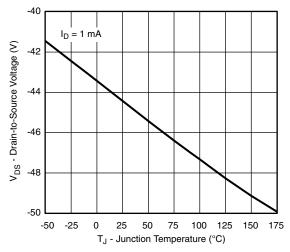
On-Resistance vs. Gate-to-Source Voltage



**Source Drain Diode Forward Voltage** 



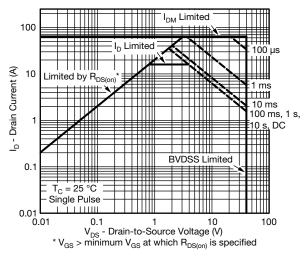
Threshold Voltage



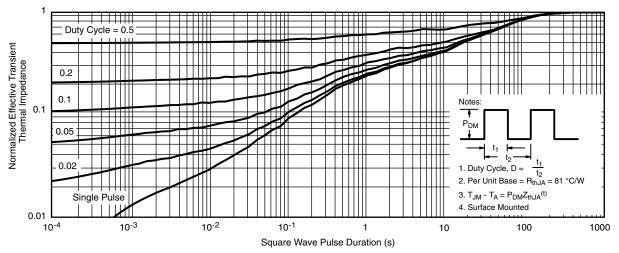
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



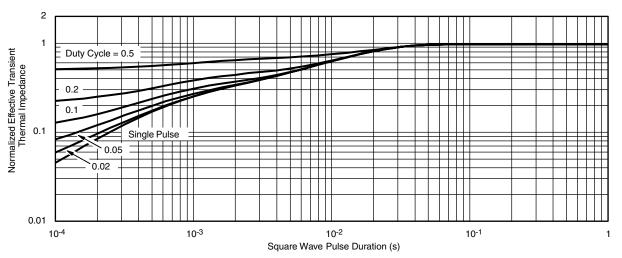
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

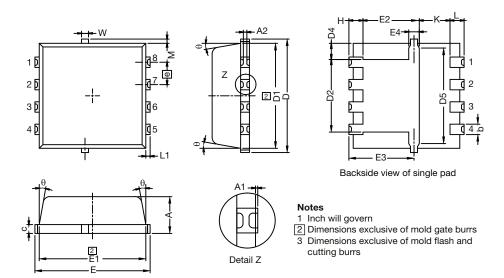
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267977">www.vishay.com/ppg267977</a>.



# PowerPAK® 1212-8W Case Outline



DIM.		MILLIMETERS			INCHES			
DIIVI.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
Α	0.97	1.04	1.12	0.038	0.041	0.044		
A1	0	-	0.05	0	-	0.002		
A2	0	-	0.13	0	-	0.005		
b	0.23	0.30	0.41	0.009	0.012	0.016		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	3.20	3.30	3.40	0.126	0.130	0.134		
D1	2.95	3.05	3.15	0.116	0.120	0.124		
D2	1.98	2.11	2.24	0.078	0.083	0.088		
D4	0.47 typ.			0.0185 typ.				
D5	2.3 typ.			0.090 typ.				
E	3.20	3.30	3.40	0.126	0.130	0.134		
E1	2.95	3.05	3.15	0.116	0.120	0.124		
E2	1.47	1.60	1.73	0.058	0.063	0.068		
E3	1.75	1.85	1.98	0.069	0.073	0.078		
E4		0.34 typ.		0.013 typ.				
е		0.65 BSC.		0.026 BSC				
K		0.86 typ.		0.034 typ.				
Н	0.30	0.41	0.51	0.012	0.016	0.020		
L	0.30	0.43	0.56	0.012	0.017	0.022		
L1	0.06	0.13	0.20	0.002	0.005	0.008		
θ	0°	-	12°	0°	-	12°		
W	0.15	0.25	0.36	0.006	0.010	0.014		
М	0.125 typ.				0.005 typ.			

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